

BF422

Rev.E Mar.-2016

TO-92

NPN

Silicon NPN transistor in a TO-92 Plastic Package.

, BF423

High breakdown voltage, complementary pair with BF423.

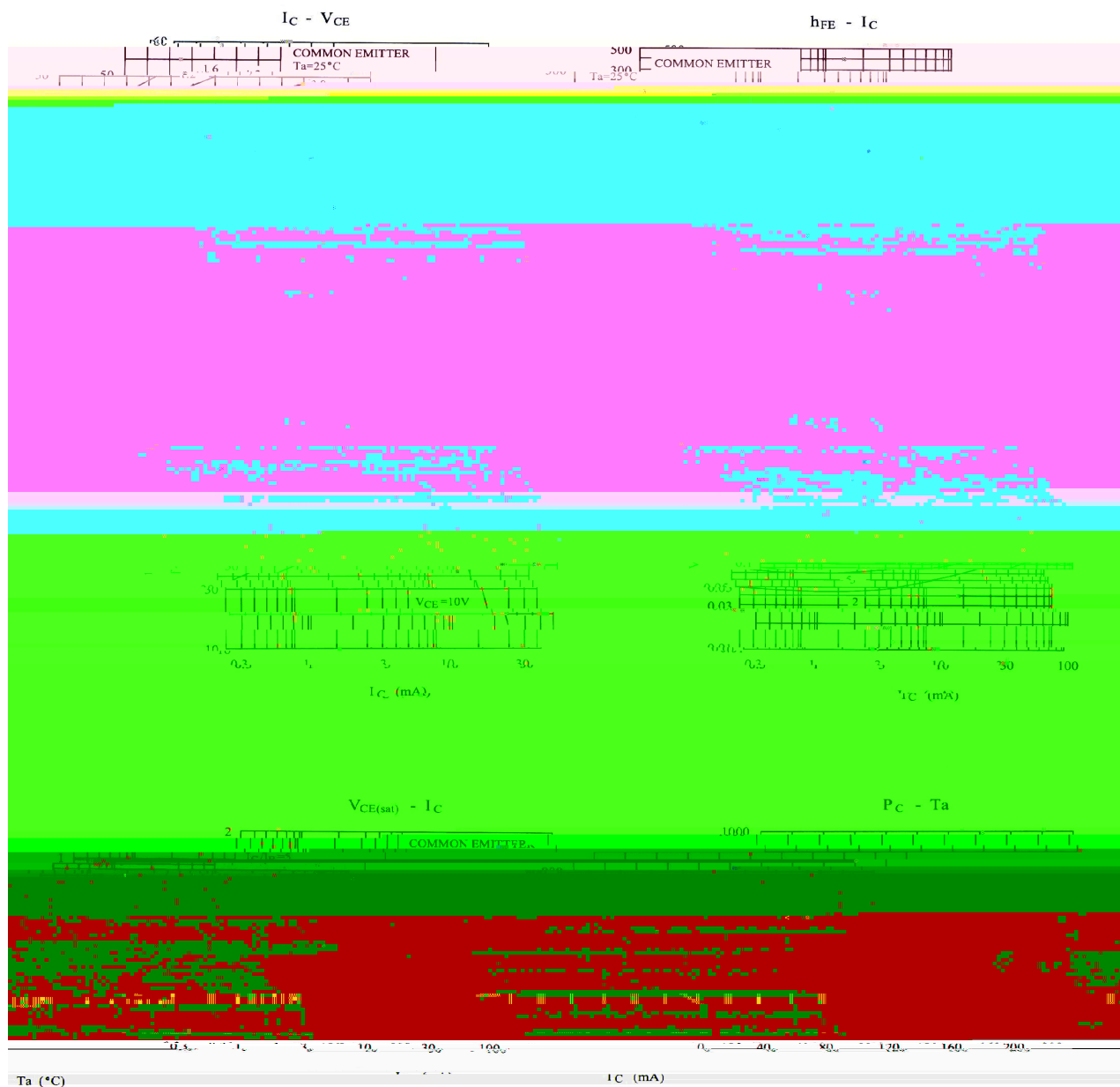
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	250	V
Collector to Emitter Voltage	V_{CEO}	250	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	50	mA
Peak Collector Current	I_{CM}	100	mA
Collector Power Dissipation	P_C	830	mW
Peak Base Current	I_{BM}	50	mA
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-off Current	I_{CBO}	$V_{CB}=200V$ $I_E=0$			0.01	μA
C Emitter Cut-off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			0.05	μA
DC Current Gain	h_{FE}	$V_{CE}=20V$ $I_C=25mA$	50			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=30mA$ $I_B=5.0mA$			0.6	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=20V$ $I_C=25mA$		0.75		V
Transition Frequency	f_T	$V_{CE}=10V$ $I_C=10mA$	60			MHz
Reverse Transfer Capacitance	C_{re}	$V_{CB}=30V$ $f=1.0MHz$ $I_E=0$			1.6	pF

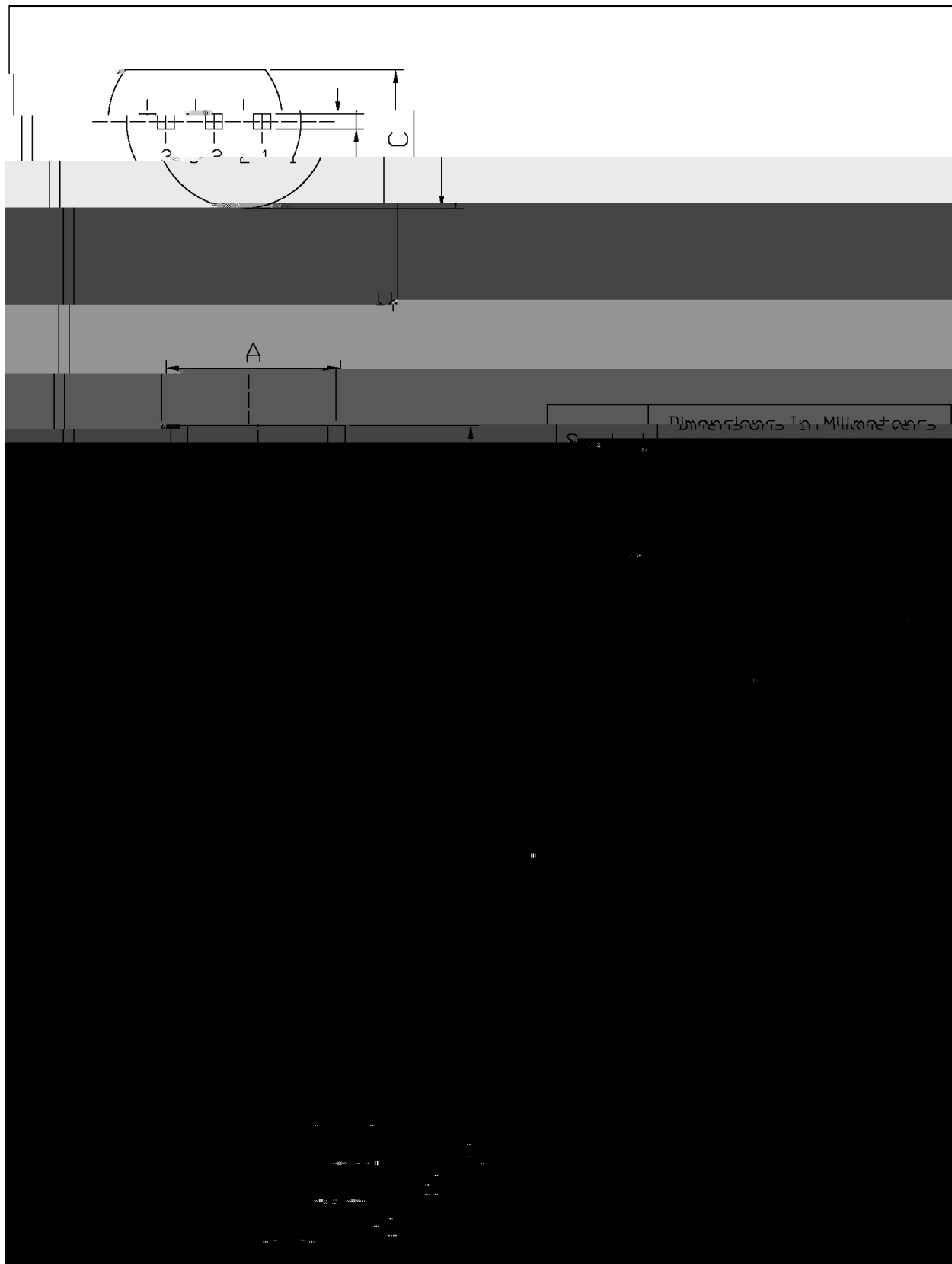
/ Electrical Characteristic Curve



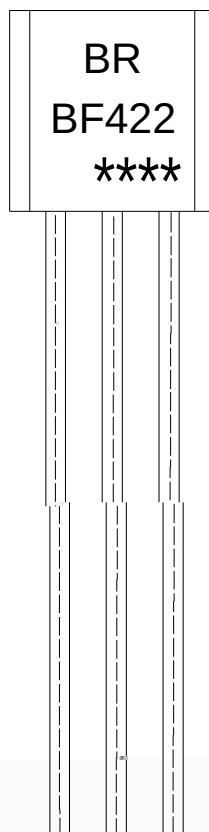
/ Package Dimensions

TO-92

Unit: mm



/ Marking Instructions



BR:

BF422

Note:

BR: Company Code.

BF422: Product Type.

****: Lot No. Code,code change with Lot No.

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DATA SHEET